

ABSTRACT

Disclosed is a method for avoiding the erosion of DRAM fuse sidewall. The method
5 comprises the steps of forming a fuse on a substrate, depositing a dielectric layer on the
substrate and the fuse, depositing operation layers on the dielectric layer to construct an
intermediate structure, applying photoresist to the intermediate structure and etching the same
to form a fuse opening so that the fuse is exposed, removing the photoresist, depositing a
separate layer to cover at least the exposed portion of the fuse, and etching the separate layer
10 so that the left separate layer covers at least the sidewall of the fuse. Disclosed also is a fuse
structure of a DRAM. The fuse structure is characterized in that the sidewall of the fuse is
covered with a separate layer having protecting function. Therefore, it is avoided that water
left at the lower portion of the fuse in cleaning step reacts with the sidewall of the fuse to
cause the damage of the structure.